CMPDM8002A

SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET



SOT-23 CASE

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPDM8002A is an Enhancement-mode P-Channel Field Effect Transistor, manufactured by the P-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications.

MARKING CODE: C802A

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

FEATURES:

- Low $r_{DS(ON)}$
- Low $V_{DS(ON)}$
- Low threshold voltage
- Fast switching
- Logic level compatibility

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Drain-Source Voltage	V_{DS}	50	V
Drain-Gate Voltage	V_{DG}	50	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	I_D	280	mA
Continuous Source Current (Body Diode)	I_S	280	mA
Maximum Pulsed Drain Current	I_{DM}	1.5	A
Maximum Pulsed Source Current	I_{SM}	1.5	A
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{GSSF}, I_{GSSR}	V_{GS}=20V, V_{DS}=0		100	nA
I_{DSS}	V_{DS}=50V, V_{GS}=0		1.0	μA
I_{DSS}	V_{DS}=50V, V_{GS}=0, T_J=125°C		500	μA
$I_{D(ON)}$	V_{GS}=10V, V_{DS}=10V	500		mA
BV_{DSS}	V_{GS}=0, I_D=10μA	50		V
$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.0	2.5	V
$V_{DS(ON)}$	V_{GS}=10V, I_D=500mA		1.5	V
$V_{DS(ON)}$	V_{GS}=5.0V, I_D=50mA		0.15	V
V_{SD}	V_{GS}=0, I_S=115mA		1.3	V
$r_{DS(ON)}$	V_{GS}=10V, I_D=500mA		2.5	Ω
$r_{DS(ON)}$	V_{GS}=10V, I_D=500mA, T_J=125°C		4.0	Ω
$r_{DS(ON)}$	V_{GS}=5.0V, I_D=50mA		3.0	Ω
$r_{DS(ON)}$	V_{GS}=5.0V, I_D=50mA, T_J=125°C		5.0	Ω

R1 (27-January 2010)

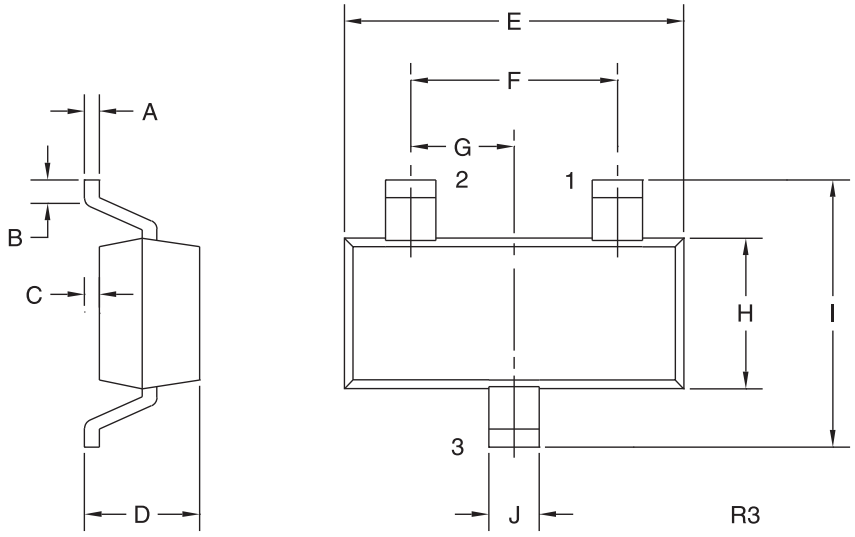
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ELECTRICAL CHARACTERISTICS - Continued: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
g_{FS}	V_{DS} =10V, I_D=200mA	200		mS
C_{rss}	V_{DS}=25V, V_{GS}=0, f=1.0MHz		7.0	pF
C_{iss}	V_{DS}=25V, V_{GS}=0, f=1.0MHz		70	pF
C_{oss}	V_{DS}=25V, V_{GS}=0, f=1.0MHz		15	pF
t_{on}, t_{off}	V_{DD}=30V, V_{GS}=10V, I_D=200mA, R_G=25Ω, R_L=150Ω		20	ns

SOT-23 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

LEAD CODE:
1) Gate
2) Source
3) Drain

MARKING CODE: C802A

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